

isc Silicon PNP Power Transistor

DESCRIPTION

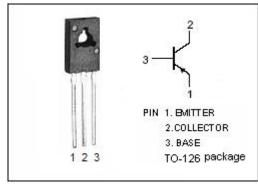
- High Collector-Emitter breakdown voltage
- Low Collector Saturation Voltage
- Complement to Type KSE340
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

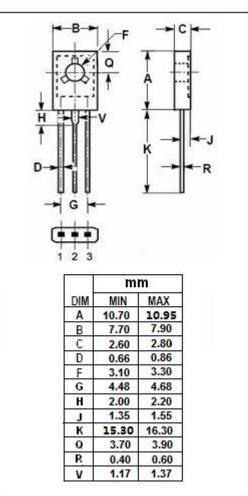
APPLICATIONS

- High voltage general purpose applications
- Suitable for transform

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage -300		V
V _{CEO}	Collector-Emitter Voltage	-300	V
V _{EBO}	Emitter-Base Voltage -5		V
Ic	Collector Current-Continuous	nt-Continuous -0.5	
Pc	Collector Power Dissipation @ T _C =25°C	20	10/
	Collector Power Dissipation @ T _a =25°C	1.3	W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$







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KSE350

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
Ісво	Collector Cutoff Current	V _{CB} = -300V; I _E = 0			-100	μА
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3V; I _C = 0			-100	μА
h _{FE}	DC Current Gain	I _C =- 50mA; V _{CE} = -10V	30		240	



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